

### **Features**

- Trench Power LV MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(on)</sub>
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

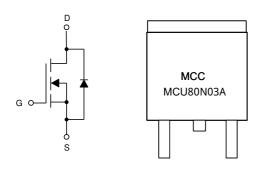
- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance: 3.3°C/W Junction to Case<sup>(Note 1)</sup>

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	V <sub>DS</sub>	30	V	
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	ı	80	Α
	T <sub>C</sub> =100°C	- I <sub>D</sub>	56	А
Pulsed Drain Current (Note 2	I <sub>DM</sub>	190	Α	
Single Pulse Avalanche Energy <sup>(Note 3)</sup>		E <sub>AS</sub>	230	mJ
Total Power Dissipation	T <sub>C</sub> =25°C	- P <sub>D</sub>	45	W
	T <sub>C</sub> =100°C	] 'D	22.5	W

#### Note:

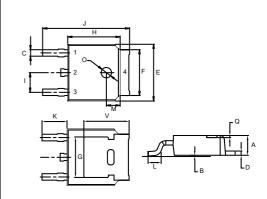
- $1.R_{\theta JA}$  is the Sum of the Junction-to-Case and Case-to-Ambient Thermal Resistance, Where the Case Thermal Reference is Defined as the Solder Mounting Surface of the Drain Pins.  $R_{\theta JC}$  is Guaranteed by Design, While  $R_{\theta JA}$  is Determined by the Board Design. The Maximum Rating Presented Here is Based on Mounting on a 1 in Pad of 2oz Copper.
- 2.Pulse Test: Pulse Width≤300µs,Duty Cycle ≤2%.
- $3.T_J=25$ °C,  $V_{DS}=30V$ ,  $V_{DD}=25V$ ,  $V_{GS}=10V$ , L=1mH.

# **Internal Structure and Marking Code**



# N-CHANNEL MOSFET

# **DPAK(TO-252)**



- Gate
- 2,4. Drain
- 3. Source

DIMENSIONS						
DIM INCHE		HES	MM		NOTE	
DIIVI	MIN	MAX	MIN	MAX	NOTE	
Α	0.087	0.094	2.20	2.40		
В	0.000	0.005	0.00	0.13		
С	0.026	0.034	0.66	0.86		
D	0.018	0.023	0.46	0.58		
E	0.256	0.264	6.50	6.70		
F	0.201	0.215	5.10	5.46		
G	0.190		4.83		TYP.	
Н	0.236	0.244	6.00	6.20		
ı	0.086	0.094	2.18	2.39		
J	0.386	0.409	9.80	10.40		
K	0.114		2.90		TYP.	
L	0.055	0.067	1.40	1.70		
M	0.063		1.60		TYP.	
0	0.043	0.051	1.10	1.30		
Q	0.000	0.012	0.00	0.30		
V	0.211		5.35		TYP.	

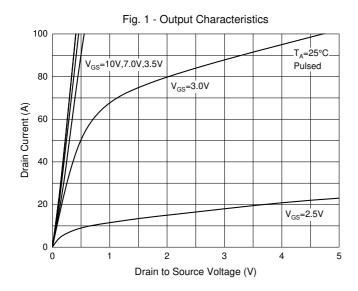


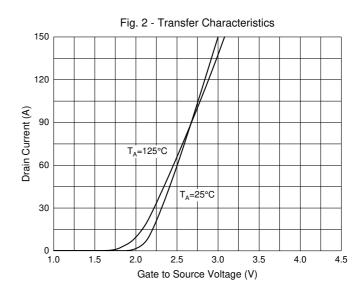
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

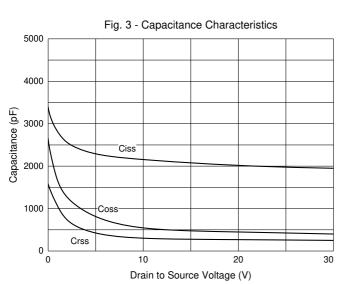
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics			ı				
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.5	V	
		V <sub>GS</sub> =10V, I <sub>D</sub> =20A		4.2	5.5		
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A		5.7	8	- mΩ	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A			1.2	V	
Continuous Body Diode Current	Is				80	Α	
Dynamic Characteristics			·				
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,f=1MHz		2150		pF	
Output Capacitance	C <sub>oss</sub>			435			
Reverse Transfer Capacitance	C <sub>rss</sub>			252			
Total Gate Charge	Qg			52.8			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =10V,I <sub>D</sub> =20A		12.3		nC	
Gate-Drain Charge	$Q_{gd}$			10.8			
Turn-On Delay Time	t <sub>d(on)</sub>			9			
Turn-On Rise Time	t <sub>r</sub>	$V_{GS}$ =10V, $V_{DD}$ =20V, $I_{D}$ =2A, $R_{L}$ =1 $\Omega$ $R_{GEN}$ =3 $\Omega$		15.5		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>			29			
Turn-Off Fall Time	t <sub>f</sub>			9			
Reverse Recovery Time	t <sub>RR</sub>	I <sub>F</sub> =20A, di/dt=100A/μs		27		ns	
Reverse Recovery Charge	$Q_{RR}$	15-20M, 41/41-100M/45		28		nC	

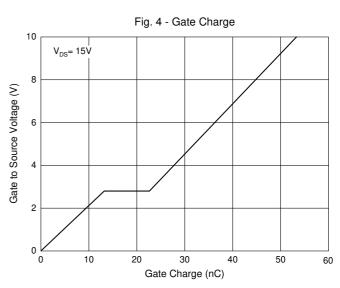


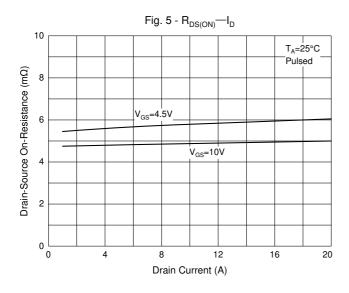
## **Curve Characteristics**

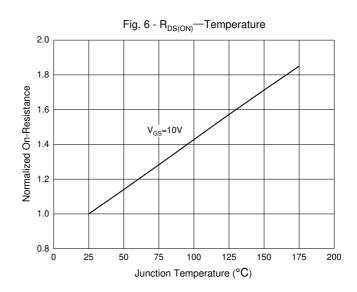














## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

Note: Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF

#### \*\*\*IMPORTANT NOTICE\*\*\*

*Micro Commercial Components Corp.* reserves the right to make changes without further notice to any product herein to make corrections, modifications, enhancements, improvements, or other changes. *Micro Commercial Components Corp*. does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold *Micro Commercial Components Corp*, and all the companies whose products are represented on our website, harmless against all damages. *Micro Commercial Components Corp*, products are sold subject to the general terms and conditions of commercial sale, as published at

## https://www.mccsemi.com/Home/TermsAndConditions.

#### \*\*\*LIFE SUPPORT\*\*\*

MCC's products are not authorized for use as critical components in life support devices or systems without the express written approval of Micro Commercial Components Corporation.

#### \*\*\*CUSTOMER AWARENESS\*\*\*

Counterfeiting of semiconductor parts is a growing problem in the industry. Micro Commercial Components (MCC) is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. MCC strongly encourages customers to purchase MCC parts either directly from MCC or from Authorized MCC Distributors who are listed by country on our web page cited below. Products customers buy either from MCC directly or from Authorized MCC Distributors are genuine parts, have full traceability, meet MCC's quality standards for handling and storage. MCC will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. MCC is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

Rev.3-3-04092022 4/4 MCCSEMI.COM